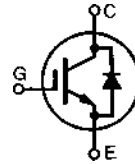


Low $V_{CE(sat)}$ IGBT with Diode
High speed IGBT with Diode

IXGH 17 N100U1
IXGH 17 N100AU1

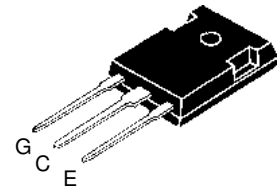
V_{CES}	I_{C25}	$V_{CE(sat)}$
1000 V	34 A	3.5 V
1000 V	34 A	4.0 V

Combi Packs



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	1000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	34	A
I_{C90}	$T_C = 90^\circ\text{C}$	17	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	68	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 82\ \Omega$ Clamped inductive load, $L = 100\ \mu\text{H}$	$I_{CM} = 34$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	150	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Weight		6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard package JEDEC TO-247 AD
- IGBT and anti-parallel FRED in one package
- 2nd generation HDMOS™ process
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- MOS Gate turn-on
 - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
 - soft recovery with low I_{RM}

Applications

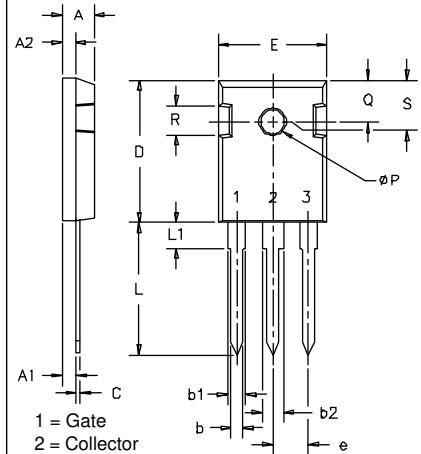
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Saves space (two devices in one package)
- Easy to mount (isolated mounting screw hole)
- Reduces assembly time and cost

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 4.5\text{ mA}$, $V_{GE} = 0\text{ V}$	1000		V
$V_{GE(th)}$	$I_C = 500\ \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$			500 μA 8 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$			3.5 V 4.0 V
				17N100U1 17N100AU1

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	I _C = I _{C90} ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	6	15	S
C_{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		1500	pF
C_{oes}			210	pF
C_{res}			40	pF
Q_g	I _C = I _{C90} , V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		100	120 nC
Q_{ge}			20	30 nC
Q_{gc}			60	90 nC
t_{d(on)}	Inductive load, T_J = 25°C		100	ns
t_{ri}	I _C = I _{C90} , V _{GE} = 15 V, L = 300 μH, V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 82 Ω		200	ns
t_{d(off)}		Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G	500	1000
t_{fi}		17N100U1	750	ns
E_{off}		17N100AU1	450	750 ns
E_{off}		17N100AU1	3	mJ
t_{d(on)}	Inductive load, T_J = 125°C		100	ns
t_{ri}	I _C = I _{C90} , V _{GE} = 15 V, L = 300 μH, V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 82 Ω		200	ns
E_{on}		Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G	700	1000
t_{d(off)}		17N100U1	1200	2000 ns
t_{fi}		17N100AU1	750	1000 ns
E_{off}		17N100U1	8	mJ
E_{off}		17N100AU1	6	mJ
R_{thJC}				0.83 K/W
R_{thCK}			0.25	K/W

TO-247 AD Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.7	5.3
A1	.087	.102	2.2	2.54
A2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b1	.065	.084	1.65	2.13
b2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.177		4.50	
øP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V_F	I _F = I _{C90} , V _{GE} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			2.5 V
I_{RM}	I _F = I _{C90} , V _{GE} = 0 V, -di _F /dt = 240 A/μs V _R = 540 V I _F = 1 A; -di _F /dt = 100 A/μs; V _R = 30 V		16	18 A
t_{tr}			120	ns
		T _J = 125°C	35	50 ns
R_{thJC}				1 K/W

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 IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Fig. 1 Saturation Characteristics

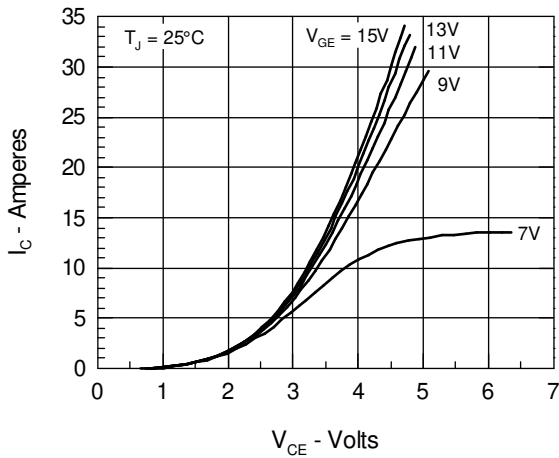


Fig. 2 Output Characteristics

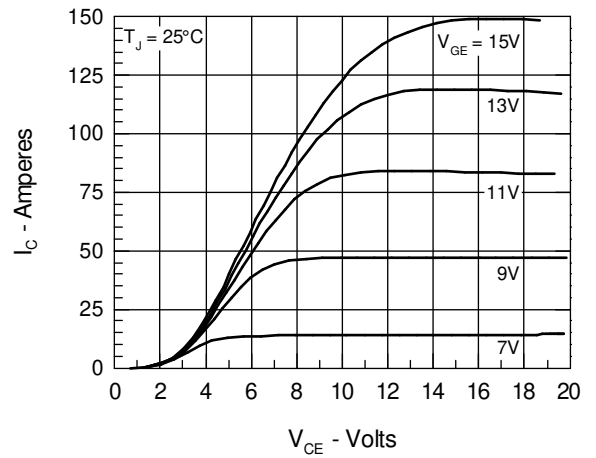


Fig. 3 Collector-Emitter Voltage vs. Gate-Emitter Voltage

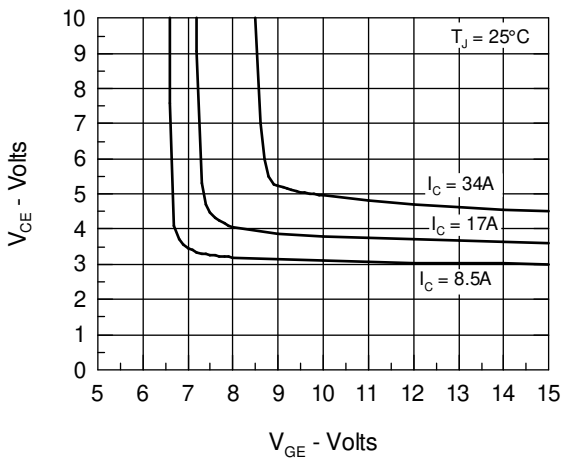


Fig. 4 Temperature Dependence of Output Saturation Voltage

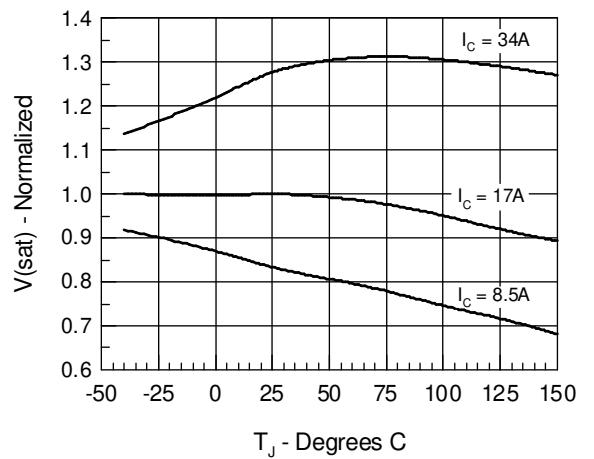


Fig. 5 Input Admittance

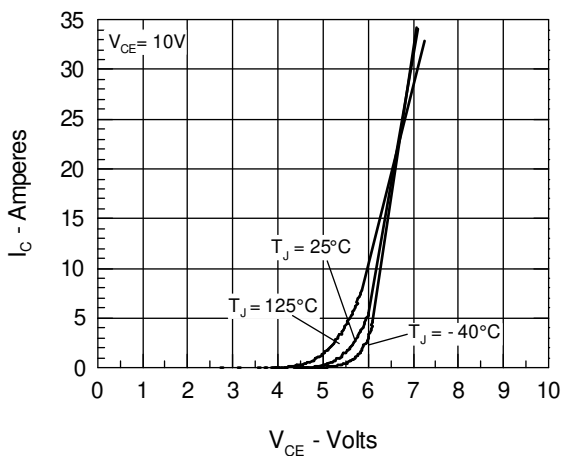


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

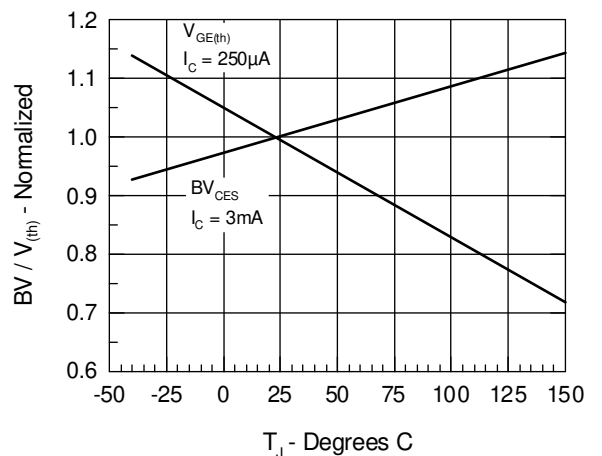


Fig.7 Gate Charge

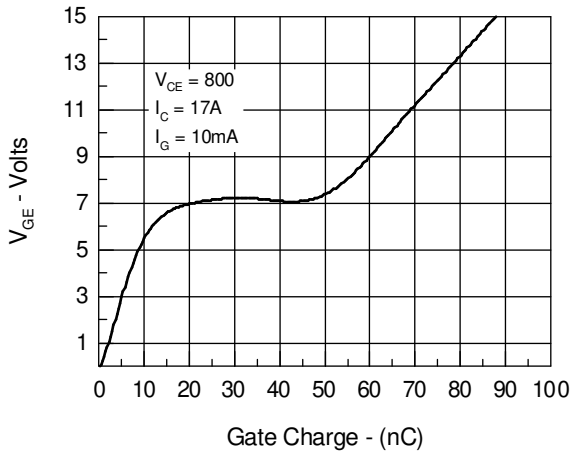


Fig.8 Turn-Off Safe Operating Area

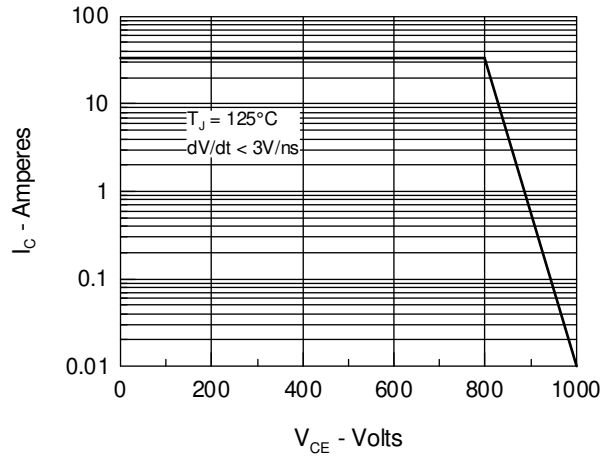


Fig.9 Capacitance Curves

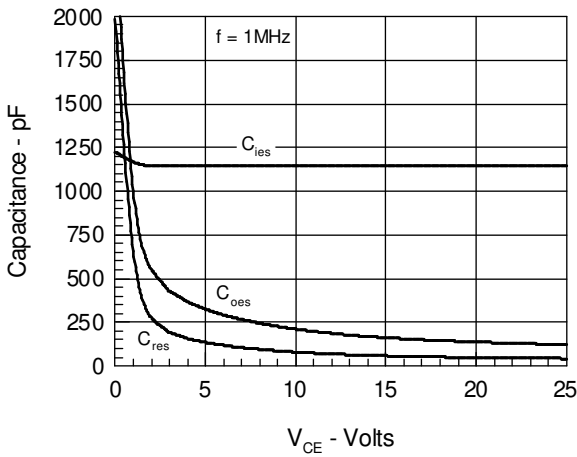
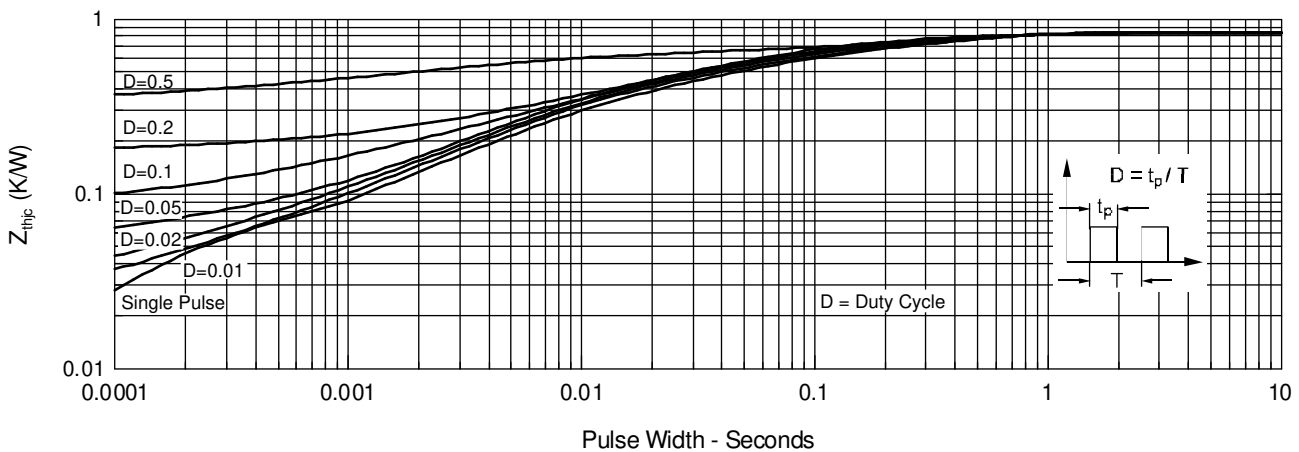


Fig.10 Transient Thermal Impedance



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4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Fig.11 Maximum Forward Voltage Drop

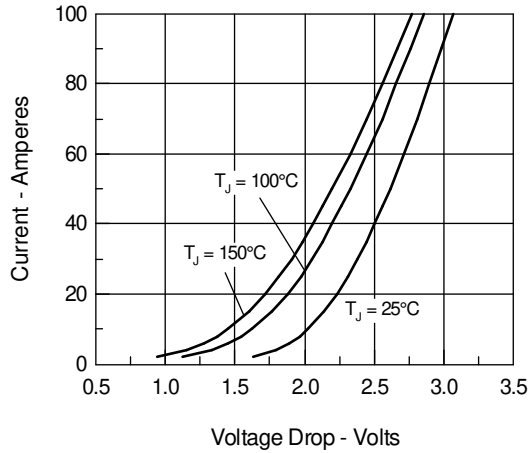


Fig.12 Peak Forward Voltage V_{FR} and Forward Recovery Time t_{FR}

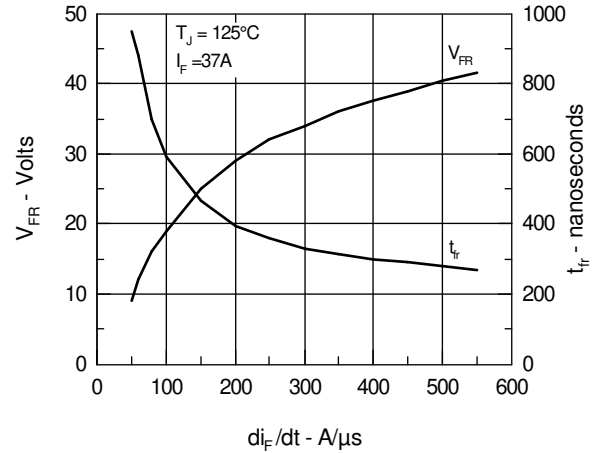


Fig.13 Junction Temperature Dependence of I_{RM} and Q_r

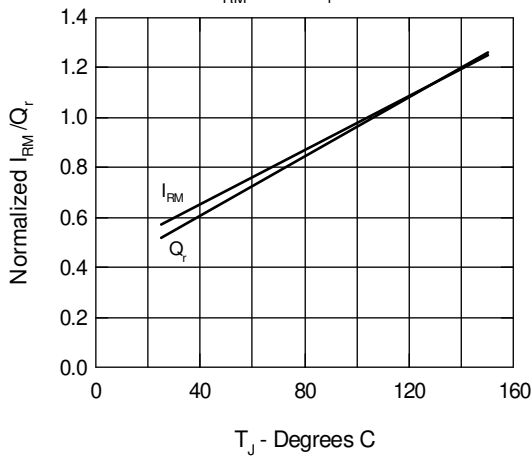


Fig.14 Reverse Recovery Charge

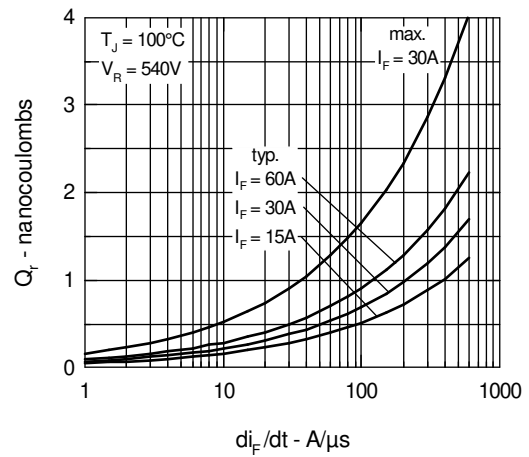


Fig.15 Peak Reverse Recovery Current

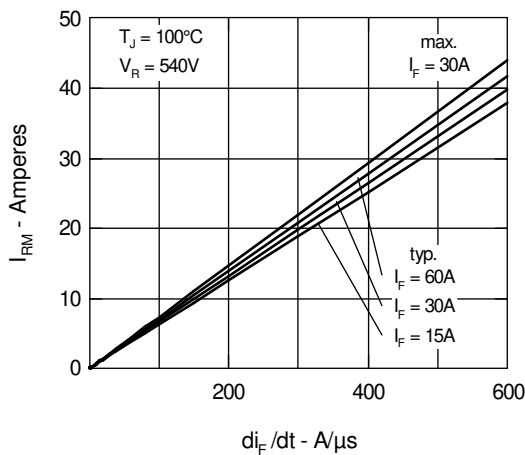


Fig.16 Reverse Recovery Time

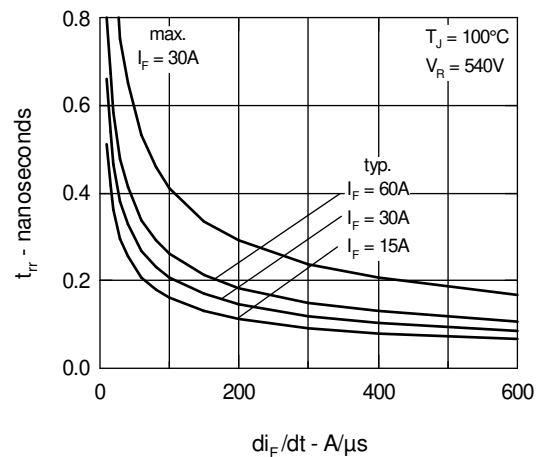
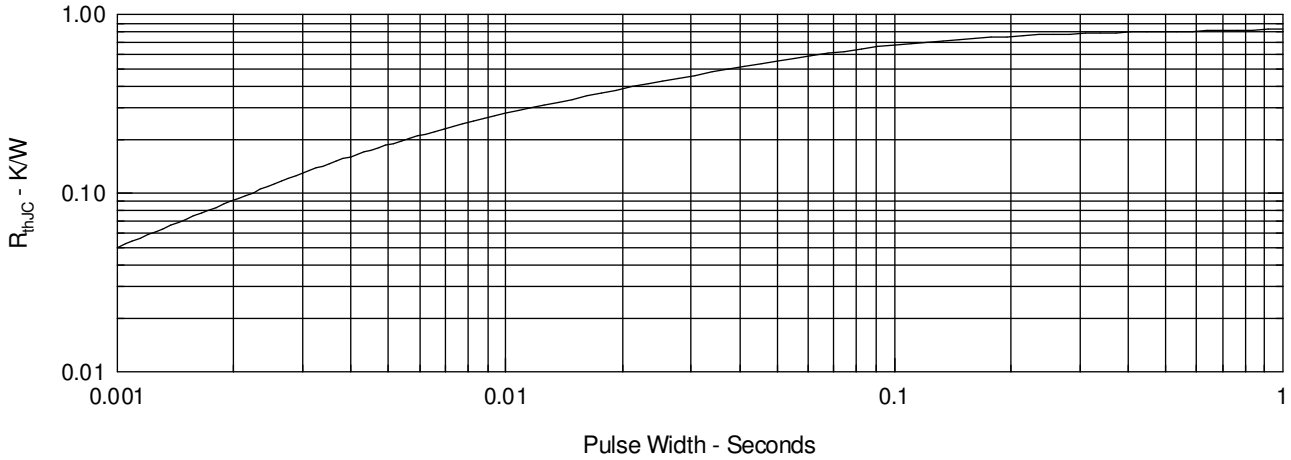


Fig.17 Diode Transient Thermal resistance junction to case



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4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025